

SANYO

No.3828

2SK1733

N-Channel MOS Silicon FET

Very High-Speed
Switching Applications

Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Meets radial taping.

Absolute Maximum Ratings at Ta = 25°C

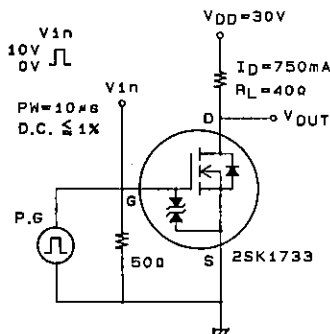
			unit
Drain to Source Voltage	V _{DSS}	60	V
Gate to Source Voltage	V _{GSS}	±15	V
Drain Current(DC)	I _D	1.5	A
Drain Current(Pulse)	I _{DP}	6	A
Allowable Power Dissipation	P _D	1	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

PW ≤ 10μs, duty cycle ≤ 1%

Electrical Characteristics at Ta = 25°C

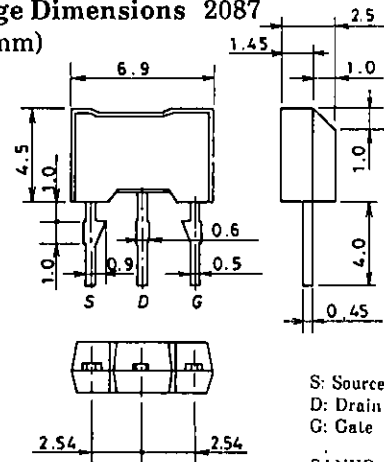
			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D = 1mA, V _{GS} = 0	60			V
Zero Gate Voltage	I _{DSS}	V _{DS} = 60V, V _{GS} = 0			100	μA
Drain Current	I _{DSS}	V _{DS} = 60V, V _{GS} = 0			100	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±12V, V _{DS} = 0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} = 10V, I _D = 1mA	1.0		2.0	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = 10V, I _D = 750mA	1.0	1.8		S
Static Drain to Source on State Resistance	R _{DS(on)}	I _D = 750mA, V _{GS} = 10V		0.35	0.45	Ω
on State Resistance	R _{DS(on)}	I _D = 750mA, V _{GS} = 4V		0.45	0.6	Ω
Input Capacitance	C _{iss}	V _{DS} = 20V, f = 1MHz		150		pF
Output Capacitance	C _{oss}	V _{DS} = 20V, f = 1MHz		60		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = 20V, f = 1MHz		12		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		6		ns
Rise Time	t _r	∕		10		ns
Turn-OFF Delay Time	t _{d(off)}	∕		60		ns
Fall Time	t _f	∕		20		ns
Diode Forward Voltage	V _{SD}	I _S = 1.5A, V _{GS} = 0		0.9		V

Switching Time Test Circuit



Package Dimensions 2087

(unit : mm)

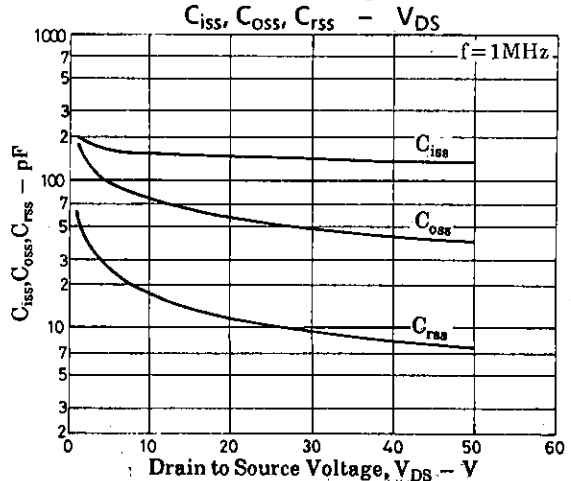
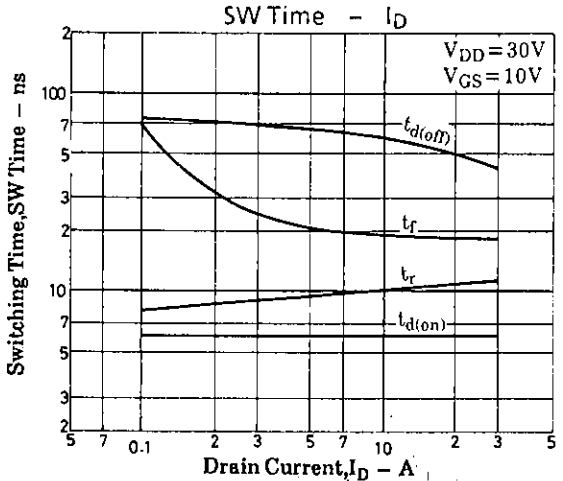
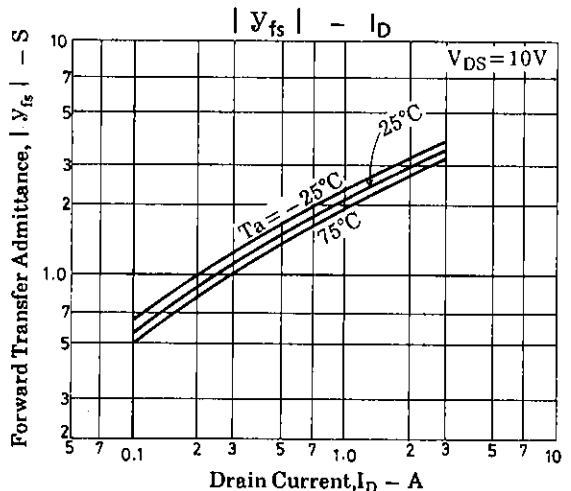
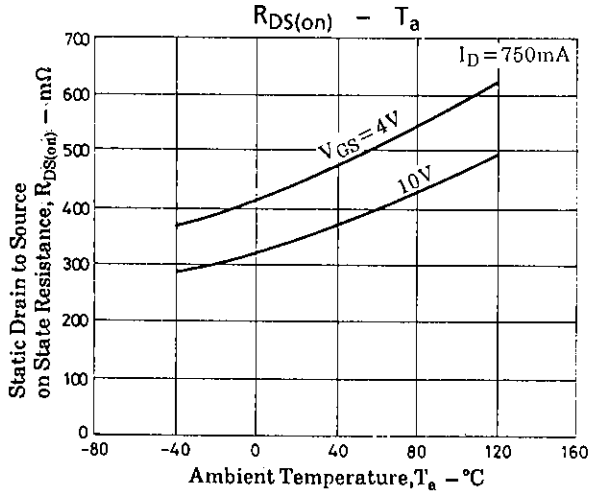
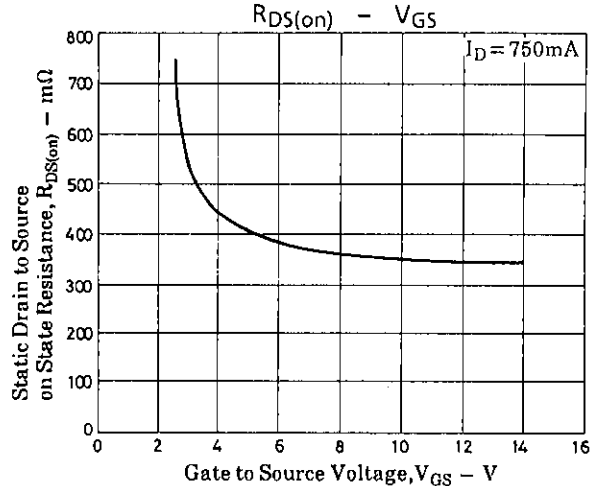
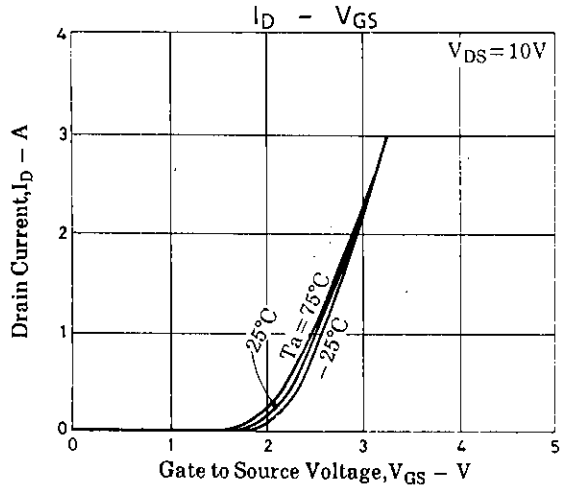
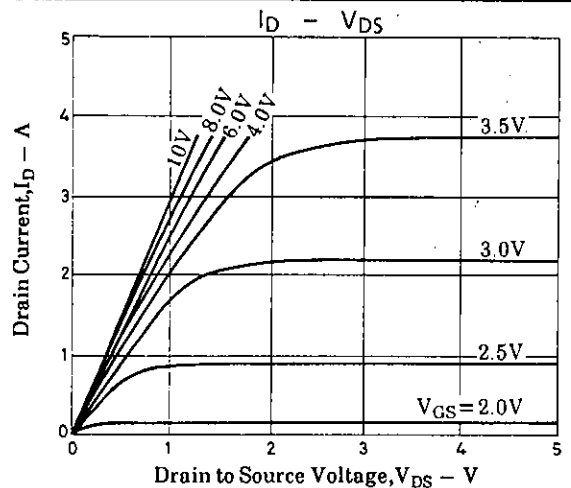
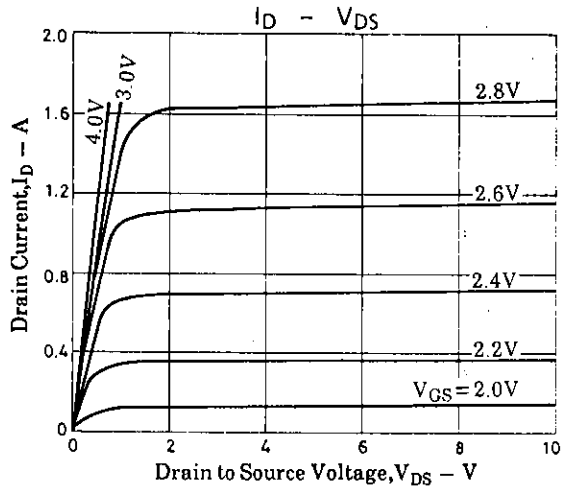


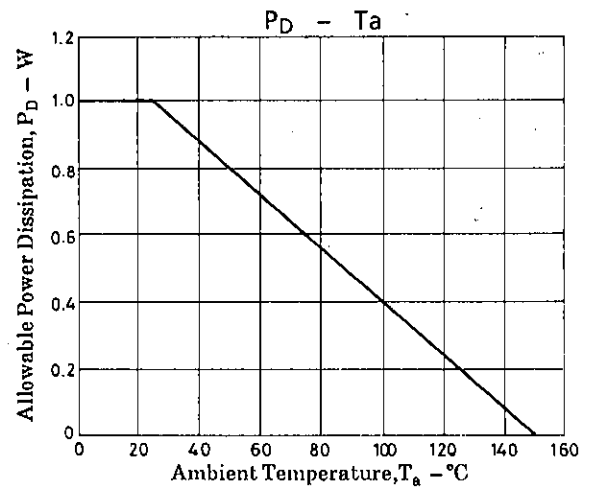
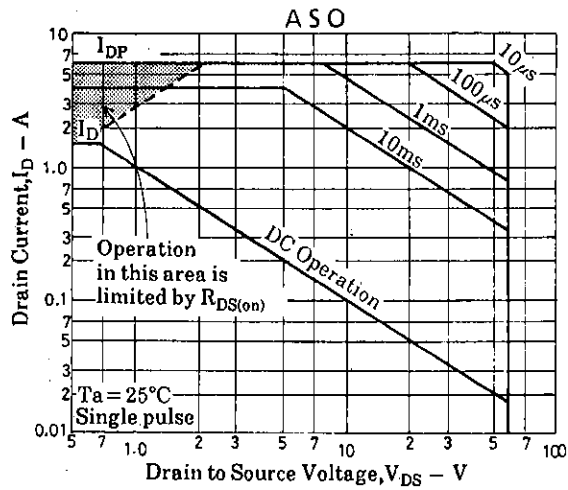
S: Source
D: Drain
G: Gate

SANYO: NMP

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